

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	IS&R	L1	4	((("20020137323") or ("6306765"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:03			
2	IS&R	L2	0	("(form\$3 or deposit\$3) same (carbon and nitrogen and hydrogen) same semiconductor").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:06			
3	BRS	L3	1322	(form\$3 or deposit\$3) same (carbon and nitrogen and hydrogen) same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:11			
4	BRS	L4	815	3 and @pd<="20031204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:10			
5	BRS	L5	205	(form\$3 or deposit\$3) same (carbon and nitrogen and hydrogen) same semiconductor same (insulat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:09			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
6	BRS	L6	125	5 and @pd<="20031204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:12			
7	BRS	L7	1044	((form\$3 or deposit\$3) same (silicon and carbon and nitrogen and hydrogen) same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:15			
8	BRS	L8	632	7 and @pd<="20031204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:17			
9	BRS	L9	2	"20040166680"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:14			
10	BRS	L10	336	((form\$3 or deposit\$3) with (silicon and carbon and nitrogen and hydrogen)) same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:17			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
11	BRS	L11	477	((form\$3 or deposit\$3) with (silicon and carbon and oxygen and hydrogen)) same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:18			
12	BRS	L12	240	10 and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:17			
13	BRS	L13	158	12 and @pd<="20031204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:19			
14	BRS	L14	83	((form\$3 or deposit\$3) with (silicon and carbon and nitrogen and hydrogen)) same semiconductor same insulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:17			
15	BRS	L15	142	((form\$3 or deposit\$3) with (silicon and carbon and oxygen and hydrogen)) same semiconductor same insulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:48			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
16	BRS	L16	86	15 and @pd<="20031204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:49			
17	BRS	L17	1013	deposit\$3 same ((first and second with chamber) same insulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:48			
18	BRS	L18	17	15 and 17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:48			
19	BRS	L19	9	18 and @pd<="20031204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:55			
20	BRS	L20	97	MIYAJIMA-HIDESHI.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:56			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
21	BRS	L21	38	HIGASHI-KAZUYUKI.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:58			
22	BRS	L22	120	FUJITA-KEIJI.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:59			
23	BRS	L23	510	HASEGAWA-TOSHIAKI.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 21:59			
24	BRS	L24	16	TABUCHI-KIYOTAKA.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/06/06 22:00			